

Title (en)
LIGHT EMITTING DIODE CHIP

Title (de)
LED-CHIP

Title (fr)
PUCE À DIODE ÉLECTROLUMINESCENTE

Publication
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Application
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Abstract (en)
Exemplary embodiments of the present invention provide light emitting diode (LED) chips and a method of fabricating the same. An LED chip according to an exemplary embodiment includes a substrate; a light emitting structure arranged on the substrate, and an alternating lamination bottom structure arranged under the substrate. The alternating lamination bottom structure includes a plurality of dielectric pairs, each of the dielectric pairs including a first material layer having a first refractive index and a second material layer having a second refractive index, the first refractive index being greater than the second refractive index.

IPC 8 full level
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C-Set (source: CN EP US)
CN US
1. **H01L 2224/48091 + H01L 2924/00014**
2. **H01L 2224/73265 + H01L 2224/32245 + H01L 2224/48247 + H01L 2924/00**
EP
1. **H01L 2224/48091 + H01L 2924/00014**
2. **H01L 2224/73265 + H01L 2224/32245 + H01L 2224/48247 + H01L 2924/00012**

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